



30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
30V	0.11Ω @ V _{GS} = 10V	4.7A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Audio Output Stage
- Relay and Solenoid Driving
- Motor Control

Features and Benefits

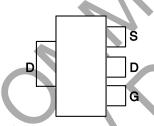
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

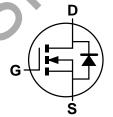
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)







Pin Out - Top



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXM62N03GTA	ZXM62N03	7	12	1,000
ZXM62N03GTC	ZXM62N03	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

ZXM6 & 2N03 &

SOT223

ZXM62N03 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5 = 2015) WW or \overline{W} W = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (V _{GS} = 10V, T _A = +25°C) (Note 6)		4.7		
$(V_{GS} = 10V, T_A = +70^{\circ}C)$ (Note 6)	I_{D}	3.8	Α	
(V _{GS} = 10V, T _A = +25°C) (Note 5)		3.4		
Pulsed Drain Current (Note 7)	I _{DM}	16	Α	
Continuous Source Current (Body Diode) (Note 6)	Is	2.6	A	
Pulsed Source Current (Body Diode) (Note 7)	I _{SM}	16	А	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	2.0 16	W mW/°C
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	Pp	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{eJA}	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	32	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

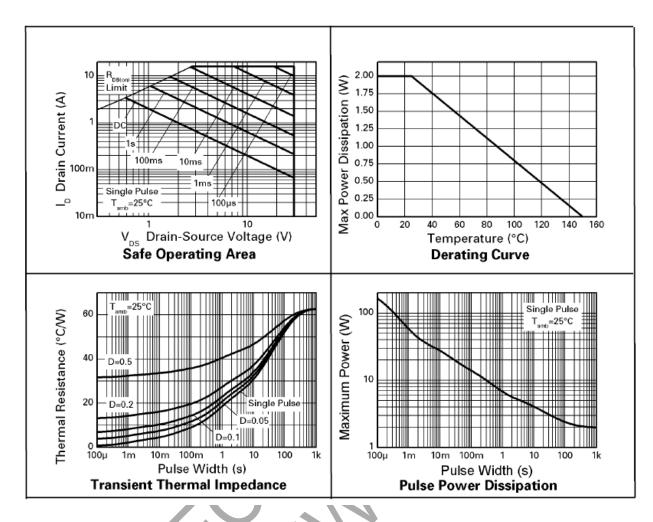
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	1	_	_	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}		_	0.11 0.15	Ω	$V_{GS} = 10V$, $I_D = 2.2A$ $V_{GS} = 4.5V$, $I_D = 1.1A$	
Forward Transconductance (Notes 8 & 10)	gfs	1.1	_	_	S	$V_{DS} = 15V, I_D = 1.1A$	
Diode Forward Voltage (Note 8)	V _{SD}	_	_	0.95	V	$T_J = +25^{\circ}C$, $I_S = 2.2A$, $V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	380	_	pF	V 25V V 2V	
Output Capacitance	Coss	_	90	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	30	_	pF		
Turn-On Delay Time (Note 9)	t _{D(ON)}		2.9	_	ns		
Turn-On Rise Time (Note 9)	t_R	_	5.6	_	ns	$V_{DD} = 15V$, $I_D = 2.2A$, $V_{GS} = 10V$,	
Turn-Off Delay Time (Note 9)	t _{D(OFF)}	_	11.7	_	ns	$R_{GS} = 6\Omega$	
Turn-Off Fall Time (Note 9)	t _F	_	6.4	_	ns		
Total Gate Charge (Note 9)	Qg	_	_	9.6	nC	V _{DS} = 24V, V _{GS} = 10V, I _D = 2.2A	
Gate-Source Charge (Note 9)	Q _{gs}	_	_	1.7	nC		
Gate-Drain Charge (Note 9)	Q _{gd}	_	_	2.8	nC		
Reverse Recovery Time	t _{RR}	_	18.8	_	ns	$T_J = +25^{\circ}C$, $I_F = 2.2A$, $di/dt =$	
Reverse Recovery Charge	Q_{RR}	_	11.4	_	nC	100A/µs	

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR-4 PCB measured at t ≤ 10 seconds.
- To a device surface modified of TR-4 PCB measured at €2 10 seconds.
 Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05 pulse width limited by maximum junction temperature.
 Measured under pulsed conditions. Width = 300µs. Duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
- 10. For design aid only, not subject to production testing.

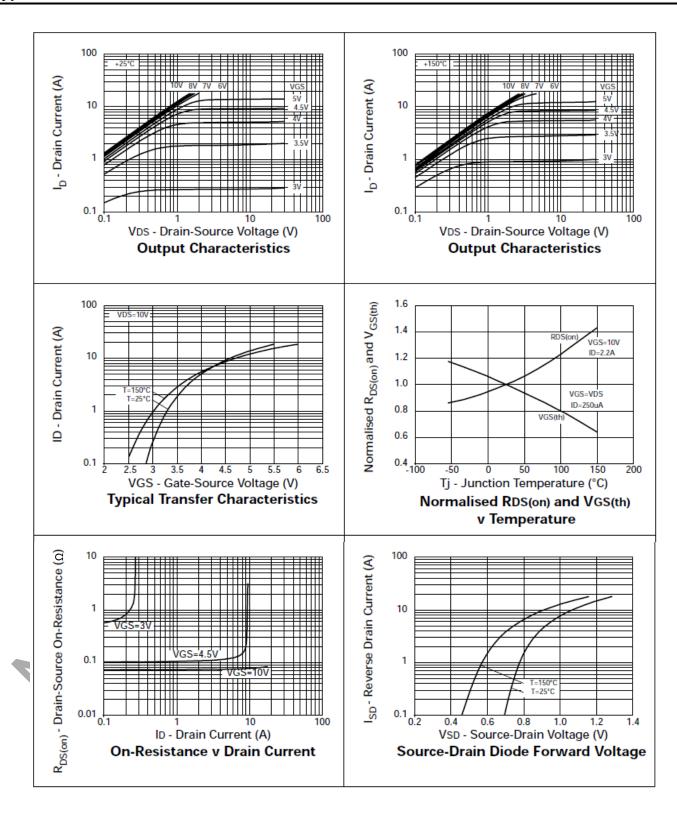








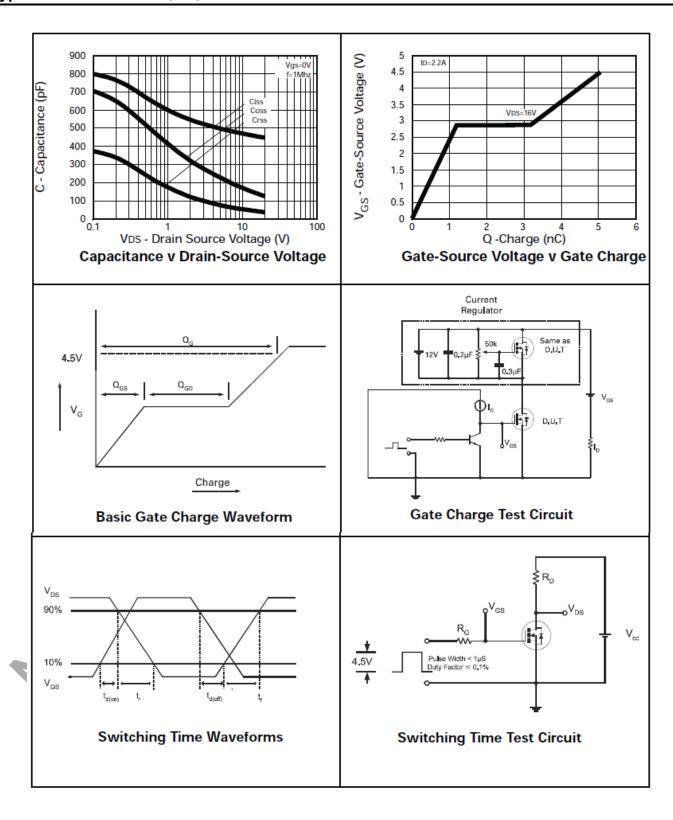
Typical Characteristics







Typical Characteristics (Cont.)

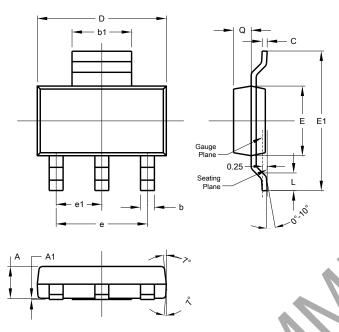




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

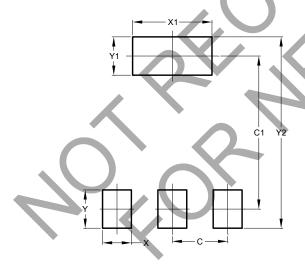


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е		-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)		
C	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		

NOT RECOMMENDED FOR NEW DESIGN USE DMN3032LE and ZXMN6A11G



ZXM62N03G

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